TO-92 Plastic-Encapsulate Transistors

FEATURE

ð Switching and Amplification in High Voltage Applications such as elephony

ð Low Current(max. 600mA)

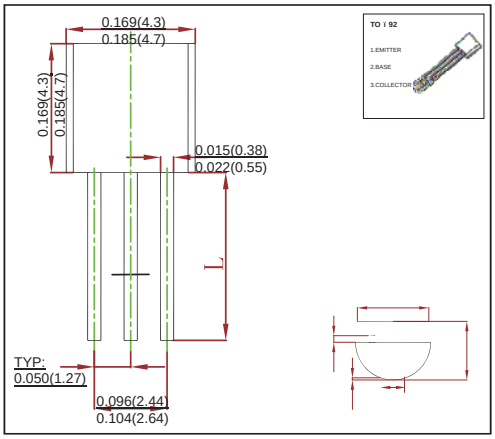
ð High Voltage(max.130v)

ð TRANSISTOR (PNP)

MECHANICAL DATA

ð Case style:TO-92 molded plastic

ð Mounting position:any



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Collector-Base Voltage	□□□□	-130	V
Collector-Emitter Voltage	□□□□	-120	V
Emitter-Base Voltage	□□□□	-5	V
Collector Current -Continuous	□□	-0.6	A
Collector Power Dissipation	□□	625	mW
	□□ □□		℃ /W
Junction Temperature	□□		℃
Storage Temperature	□□□□		

Parameter	Symbol	Test conditions	M□□	T□□		
Collector-base breakdown voltage	$V_{(BR)CBO}$					V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0				V
Emitter-base breakdown voltage	$V_{(BR)EBO}$		-5			V
Collector cut-off current	I_{CBO}				-0.1	
Emitter cut-off current	I_{EBO}					
DC current gain	h_{FE1}	V_{CE}= -5 V, I_C=-1mA	30			
	h_{FE2}	V_{CE}= -5 V, I_C= -10mA	40		180	
	h_{FE3}					

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